

1. ABSOLUTE MAXIMUM RATING (Ambient Temperature Ta=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	VDS	4	V
Gate-Source Voltage	VGS	-3	V
Total Power Dissipation *	Pt	290	mW
Storage Temperature	Tstg	-65 ~ +150	°C
Channel Temperature	Tch	150	°C

*Note: Mounted on Al2O3 board (30 x 30 x 0.65mm)

2. RECOMMENDED OPERATING CONDITION

Item	Symbol	Limit	Unit
Drain-Source Voltage	VDS	≤ 3	V
Channel Temperature	Tch	≤ +80	°C
Forward Gate Current *	IGF	≤ 0.2	mA
Reverse Gate Current *	IGR	≥ -0.075	mA

* : Rg = 4000Ω

3. ELECTRICAL CHARACTERISTICS (Ambient Temperature Ta=25°C)

Item	Symbol	Test Conditions	Limit			Unit	
			Min.	Typ.	Max.		
Saturated Drain Current	IDSS	VDS=2V, VGS=0V	15	40	85	mA	
Transconductance	gm	VDS=2V, IDS=10mA	40	60	---	mS	
Pinch-off Voltage	Vp	VDS=2V, IDS=1mA	-0.2	-1.0	-2.0	V	
Gate Source Leak Current	IGSO	VGS=-2V	---	---	-100	nA	
Gate Source Capacitance	Cgs	VDS=3V IDS=10mA	FHX35X/002	---	0.27	---	pF
			FHX35LG/002	---	0.47	---	
			FHX35LGT/002	---	0.47	---	
Drain Source Capacitance	Cgd		---	0.035	---	pF	

Note

- FHX35X/002 : Chip / Packing style: Tray
- FHX35LG/002 : LG-package / Packing style: Tray
- FHX35LGT/002 : LG-package / Packing style: Taping

RoHS Compliance	Yes
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FHX35X/002
FHX35LG/002
FHX35LGT/002

Super Low Noise HEMT

For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>